

EC104ES: ELECTRONIC DEVICES AND CIRCUITS**B.Tech. I Year I Sem.**

L	T	P	C
3	0	0	3

Course Overview: This course introduces fundamental semiconductor devices and their behavior, including diodes, BJTs, and FETs. It covers their characteristics, applications, and the analysis of basic electronic circuits. The course also explores rectifiers, voltage regulation, amplifier design, and advanced semiconductor technologies like FinFETs and CNTFETs. Emphasis is placed on developing a strong foundation for analog circuit design and understanding modern device technologies in electronics.

Course Outcomes: By the end of this course, students will be able to:

- CO1: Analyze the electrical characteristics and models of semiconductor diodes and apply them in rectifier and clipping circuits.
- CO2: Evaluate the operation and configurations of Bipolar Junction Transistors (BJTs) and analyze their input and output characteristics.
- CO3: Design appropriate biasing networks for BJTs and determine the operating point for amplifier applications.
- CO4: Analyze transistor amplifier circuits using h-parameter models and assess performance for various configurations.
- CO5: Analyze the structure, working, and characteristics of JFETs, MOSFETs, and advanced devices like FinFETs and CNTFETs, and compare modern device technologies.

Course Articulation Matrix

COs/POs	PO1	PO2	PO3	PO4	PO5	PO6	PO7	PO8	PO9	PO10	PO11
CO1	3	3	2	2	1	1	-	-	-	-	-
CO2	3	3	2	2	1	-	-	-	-	-	-
CO3	3	3	3	2	1	-	-	-	-	-	-
CO4	3	3	3	2	2	-	-	-	-	-	1
CO5	3	3	2	2	2	1	-	-	-	-	2

Syllabus:**UNIT - I:**

Diode Characteristics and Applications: PN junction diode – I-V characteristics, Diode resistance and capacitance, Diode models (Ideal, Simplified, Piecewise Linear), Rectifiers – Half-wave, Full-wave (Center-tap and bridge), Capacitor filter for rectifiers, Clippers and clamps, Zener diode – I-V characteristics and voltage regulation.

UNIT - II:

Bipolar Junction Transistor (BJT): Structure and working principle of BJT, Current components and transistor action, Configurations: Common Base (CB), Common Emitter (CE), Common Collector (CC), Input and output characteristics, Determination of h-parameters from transistor characteristics.

UNIT - III:

BJT Biasing: Need for biasing and stabilization, Load line and operating point, Biasing techniques: Fixed bias, Collector-to-base bias, Voltage divider bias, Stability factors and thermal runaway

UNIT - IV:

Transistor Amplifiers: Transistor as a small-signal amplifier, h-parameter equivalent circuit, CE, CB, CC amplifier analysis using h-parameters, Approximate CE model – with and without emitter bypass capacitor.

UNIT - V:

Special Purpose Diodes: Principle of Operation of – SCR, Tunnel Diode, Varactor Diode, Photo Diode, Solar Cell, LED and Schottky Diode

Field Effect Transistors and Advanced Devices: JFET: Structure, operation, and characteristics, MOSFET: Enhancement and Depletion modes – Structure, operation, and characteristics, Advanced Devices: FinFETs - 3D structure, Scaling advantages, CNTFETs - Structure, ballistic transport, fabrication, Comparison: CMOS vs. FinFET vs. CNTFET.

TEXT BOOKS:

1. Millman, Jacob, and Christos C. Halkias. *Electronic Devices and Circuits*. Tata McGraw-Hill, 1991.
2. Boylestad, Robert L., and Louis Nashelsky. *Electronic Devices and Circuit Theory*. Pearson, 11th ed., 2013.
3. Sedra, Adel S., and Kenneth C. Smith. *Microelectronic Circuits*. Oxford University Press, 7th ed., 2014.

REFERENCE BOOKS:

1. Bell, David A. *Electronic Devices and Circuits*. Oxford University Press, 5th ed., 2008.
2. Neamen, Donald A. *Electronic Circuit Analysis and Design*. McGraw-Hill, 2nd ed., 2001.
3. Salivahanan, S., and N. Suresh Kumar. *Electronic Devices and Circuits*. McGraw-Hill Education, 4th ed., 2017.
4. Razavi, Behzad. *Fundamentals of Microelectronics*. Wiley, 2nd ed., 2013.
5. Taur, Yuan, and Tak H. Ning. *Fundamentals of Modern VLSI Devices*. Cambridge University Press, 2nd ed., 2009.